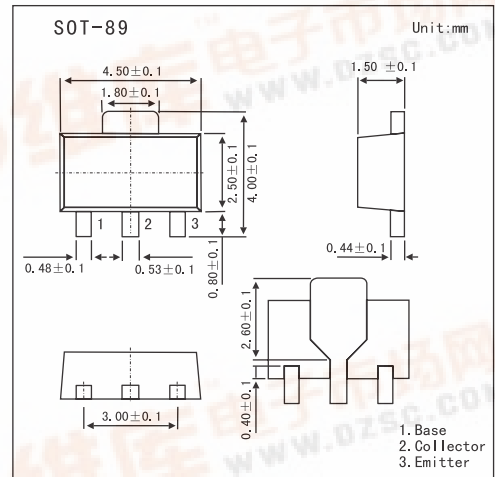


SMD Type Transistors

Silicon PNP Epitaxial
2SB1000

■ Features

- Low frequency amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	-25	V
Collector to emitter voltage	V _{CEO}	-20	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-1	A
peak collector current	I _{CP} *	-1.5	A
Collector power dissipation	P _C	1	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 ms; d ≤ 0.02.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10 μA, I _E = 0	-25			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1 mA, R _{BE} = ∞	-20			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10 μA, I _C = 0	-5			V
Collector cutoff current	I _{CBO}	V _{CB} = -20 V, I _E = 0			-0.1	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -4 V, I _C = 0			-0.1	μA
DC current transfer ratio *	h _{FE}	V _{CE} = -2 V, I _C = -0.5 A	85		240	
Collector to emitter saturation voltage *	V _{CE(sat)}	I _C = -0.8 A, I _B = -0.08 A		-0.2	-0.3	V
Base to emitter saturation voltage *	V _{BE(sat)}	I _C = -0.8 A, I _B = -0.08 A		-0.94	-1.1	V
Gain bandwidth product	f _T	V _{CE} = -2 V, I _C = -0.15 A		200		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0 f=1MHz		38		pF

■ hFE Classification

Marking	AH	AJ
hFE	85~170	120~240

